

EAST [7527.wsp:1]

File View Edit Tools Window Help

Pending Active Filtered

DBs: USPAT, US-PGPUB, EPO, JPO

Default normalize: NR

Plots Highlight all hit terms in bold

ORR form ISAR form Image Text HTML

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	<input type="checkbox"/>	<input type="checkbox"/>	US 6642073 B1	20031104	15	Semiconductor circuit and method of fabricating the same	438/30	438/164; 438/166;
2	<input type="checkbox"/>	<input type="checkbox"/>	US 6635900 B1	20031021	33	Semiconductor film having a single-crystal like region with no grain	257/72	257/49; 257/57;
3	<input type="checkbox"/>	<input type="checkbox"/>	US 6624445 B2	20030923	17	Semiconductor device and method of manufacturing the same	257/66	257/69; 257/70;
4	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6624049 B1	20030923	41	Semiconductor device and method of manufacturing the same	438/476	438/471; 438/473;
5	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6613613 B2	20030902	13	Thin film type monolithic semiconductor device	438/149	257/E21.134; 257/E21.703;
6	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6608325 B1	20030819	24	Transistor and semiconductor device having columnar crystals	257/64	257/255; 257/267;
7	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6589822 B1	20030708	9	Manufacturing method for top-gate type and bottom-gate type thin film tr	438/151	257/E21.101; 438/158;
8	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6551907 B2	20030422	11	Metal-gettering method used in the manufacture of crystalline-Si TFT	438/476	257/E21.133; 257/E21.32;
9	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6545320 B2	20030408	42	Electro-optical device and semiconductor device	257/350	257/59; 257/627;
10	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6544826 B1	20030408	16	Method for producing semiconductor device	438/166	438/308; 438/486
11	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6541793 B2	20030401	26	Thin-film transistor and semiconductor device using thin-film	257/57	257/67; 438/149;
12	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6541315 B2	20030401	21	Semiconductor device and fabrication method thereof	438/151	257/E21.133; 257/E21.318;
13	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6528820 B1	20030304	21	Semiconductor device and method of	257/66	257/347;

Start [Icons] Inbox - M... [USPTO] My Yahoo... [eDAN Ve] [EAST] [Icons] 8:12 AM

☐ Pending
☒ Active
☒ L1: (102) "5614"
☐ Failed

DBs: USPAT, US-PGPUB, EPO, JPO
 Default translator: n/a
☒ BKB form ☒ ISR form ☒ Image ☒ Text ☒ HTML

☒ Plurals
☒ Highlight all hit terms initially

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
14	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6528358 B1	20030304	123	Semiconductor device and method for fabricating the same	438/151	257/E21.133; 257/E21.192;
15	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6518102 B1	20030211	18	Method for manufacturing transistor semiconductor devices with step of a	438/143	438/153
16	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6506635 B1	20030114	28	Semiconductor device, and method of forming the same	438/148	438/166
17	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6504174 B1	20030107	122	Semiconductor device and method for fabricating the same	257/64	257/151; 257/59;
18	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6501094 B1	20021231	27	Semiconductor device comprising a bottom gate type thin film transistor	257/57	257/347; 257/59;
19	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6495886 B1	20021217	36	Semiconductor thin film and semiconductor device	257/347	257/65; 257/66;
20	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6495858 B1	20021217	29	Active matrix display device having thin film transistors	257/59	257/350; 257/72;
21	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6482686 B1	20021119	15	Method for manufacturing a semiconductor device	438/166	257/E21.703; 257/E21.111;
22	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6479331 B1	20021112	16	Method of fabricating a semiconductor device	438/153	257/E21.133; 257/E21.413;
23	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6478263 B1	20021112	22	Semiconductor device and its manufacturing method	257/51	257/347; 257/348;
24	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6465287 B1	20021015	18	Method for fabricating a semiconductor device using a metal c	438/162	257/E21.133; 257/E21.703;
25	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6465284 B2	20021015	24	Semiconductor device and method for manufacturing the same	438/151	257/E21.192; 257/E21.413;
26	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6451638 B1	20020917	17	Semiconductor and process for	438/166	117/8;

Start ☐ Inbox - M... ☒ USPTO In... ☐ My Yahoo! ☐ eDAN Ver... ☐ EAST - L... 8:12 AM

	U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
27	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6433363 B1	20020813	18	Semiconductor device and manufacturing method thereof	257/66	257/408; 257/57;
28	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6432756 B1	20020813	14	Semiconductor device and fabricating method thereof	438/166	148/DIG 90; 148/DIG 91;
29	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6417031 B2	20020709	16	Method of manufacturing a semiconductor device	438/151	257/E21.134; 257/E21.413;
30	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6413805 B1	20020702		Semiconductor device forming method	438/166	257/E21.133; 257/E21.413;
31	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6399454 B1	20020604		Method of manufacturing a semiconductor film and method of m	438/308	438/149; 438/151;
32	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6376862 B1	20020423		Semiconductor device and its manufacturing method	257/64	
33	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6368904 B1	20020409		Semiconductor device and method of manufacturing the same	438/166	257/66; 257/E21.703;
34	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6348367 B1	20020219	13	Method for manufacturing a semiconductor device	438/151	257/E21.133; 257/E21.413;
35	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6346486 B1	20020212		Transistor device and method of forming the same	438/761	257/66; 257/E21.133;
36	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6338991 B1	20020115		Semiconductor device and method for manufacturing the same	438/162	257/E21.133; 257/E21.413;
37	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6337231 B1	20020108	18	Method for producing semiconductor device	438/150	257/E21.133; 257/E21.134;
38	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6337229 B1	20020108		Method of making crystal silicon semiconductor and thin film transistor	438/149	257/E21.133; 257/E21.134;
39	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6331475 B1	20011218		Method and manufacturing	438/479	257/E21.133; 257/108;

EAST - [7527.wsp-1]

File View Edit Tools Window Help

Pending Active LI: (102) "5614" Failed

QB: USPAT, US PGPUB, EPO, JPO

Default operation: BR

BRS form ISAR form Image Text HTML

Plural Highlight all hit terms initially

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
40	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6323072 B1	20011127		Method for forming semiconductor thin film	438/166	148/DIG.1; 257/E21.133;
41	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6323071 B1	20011127		Method for forming a semiconductor device	438/162	257/E21.133; 257/E21.413;
42	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6323070 B1	20011127		Semiconductor device and its manufacturing method	438/162	438/166; 438/487
43	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6316810 B1	20011113		Display switch with double layered gate insulation and resinous interlayer	257/347	257/353; 257/408;
44	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6316789 B1	20011113		Semiconductor device and method for producing the same	257/66	257/64; 257/65;
45	<input type="checkbox"/>	<input type="checkbox"/>	US 6307214 B1	20011023	36	Semiconductor thin film and semiconductor device	257/59	257/627; 257/64;
46	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6303963 B1	20011016		Electro-optical device and semiconductor circuit	257/350	257/59; 257/627;
47	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6303415 B1	20011016		Semiconductor device and method of fabricating same	438/166	257/66; 438/164;
48	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6300659 B1	20011009		Thin-film transistor and fabrication method for same	257/347	257/49; 257/50;
49	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6297518 B1	20011002		Active matrix display and electrooptical device	257/59	257/350; 257/72;
50	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6259120 B1	20010710		Semiconductor device and method for fabricating the same	257/72	257/66; 257/E21.413;
51	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6259117 B1	20010710		Active matrix display having storage capacitor associated with each pixel	257/59	257/72; 257/E29.275;
52	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6232205 B1	20010515		Method for producing a	438/476	257/913;

Start Inbox - Micr USPTO Int. My Yahoo! eDAN Vers EAST - L... 8:12 AM

EAST - [7527.wsp:1]

File View Edit Tools Window Help

☐ Pending
☒ Active
☒ L1: (102) "3614"
☒ Failed

DB: USPAT, US-PGPUB, EPO, JPO

Default criteria: OR

☒ Plurals
☒ Highlight all hit terms initially

☒ BRS term ☒ ESR term ☒ Image ☒ Text ☒ HTML

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
53	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 6225645 B1	20010501		Semiconductor device and method of manufacturing the same	257/59	257/347; 257/348;
54	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 6225152 B1	20010501		Semiconductor device and fabrication method thereof	438/162	257/E21.133; 257/E21.318;
55	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 6218702 B1	20010417		Microcrystal silicon film and its manufacturing method, and photoelec	257/347	257/50; 257/51;
56	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 6210997 B1	20010403		Semiconductor device and method for manufacturing the same	438/151	257/E21.192; 257/E21.413;
57	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 6204101 B1	20010320		Method of manufacturing semiconductor device	438/166	257/E21.133; 257/E21.318;
58	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 6194254 B1	20010227		Semiconductor device and method for manufacturing the same	438/166	257/E21.703; 257/E27.111;
59	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 6180439 B1	20010130		Method for fabricating a semiconductor device	438/162	257/E21.133; 257/E21.703;
60	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 6169292 B1	20010102		Thin film type monolithic semiconductor device	257/72	257/155; 257/157;
61	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 6168980 B1	20010102		Semiconductor device and method for forming the same	438/162	257/E21.192; 257/E21.268;
62	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 6156590 A	20001205		Method for producing semiconductor device	438/166	438/308; 438/471;
63	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 6140165 A	20001031		Semiconductor device forming method	438/166	257/E21.133; 257/E21.413;
64	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 6133119 A	20001017		Photoelectric conversion device and method manufacturing same	438/476	438/471; 438/764
65	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 6110770 A	20000829		Semiconductor and process for	438/166	117/7;

Inbox - Micr... ☒ USPTO Intr... ☒ My Yahoo! ☒ eDAN Vers... ☒ EAST - L...

8:12 AM

EAST - [7527.wsp.1]

File View Edit Tools Window Help

Pending
Active
L1: (102) "5614"
Failed

DB: USPAT, US, PGPUB, EPO, JPO
Default database: DB
BRB form
ISR form
Image
Text
HTML

Plural
Highlight all hit terms initially

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
66	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6104547 A	20000815		Zoom lens and optical apparatus having the same	359/687	359/676
67	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6100562 A	20000808		Method of manufacturing a semiconductor device	257/347	257/49; 257/50;
68	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6093937 A	20000725		Semiconductor thin film, semiconductor device and manufacture	257/59	257/58; 257/60;
69	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6093934 A	20000725		Thin film transistor having grain boundaries with segregated oxygen a	257/51	257/347; 257/353;
70	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6087679 A	20000711		Semiconductor thin film and semiconductor device	257/65	257/66; 257/E21.133;
71	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6084247 A	20000704		Semiconductor device having a catalyst enhanced crystallized layer	257/58	257/347; 257/348;
72	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6077731 A	20000620		Semiconductor device and method for fabricating the same	438/150	257/E21.133; 257/E21.703;
73	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6072193 A	20000606		Thin-film transistor and semiconductor device using thin-film	257/57	257/347; 257/348;
74	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6066518 A	20000523		Method of manufacturing semiconductor devices using a crystal	438/166	257/E21.703; 438/491
75	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6063654 A	20000516		Method of manufacturing a thin film transistor involving laser treatment	438/166	257/E21.192; 257/E21.413;
76	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6037635 A	20000314		Semiconductor device with transistors formed on different layers	257/353	257/351; 257/352;
77	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6037610 A	20000314		Transistor and semiconductor device having columnar crystals	257/64	257/255; 257/627;
78	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6028326 A	20000222		Thin film transistor including a	257/66	257/335;

Start
Inbox - Micr...
USPTO Intr...
My Yahoo!
eDAN Versi...
EAST - L...
8:12 AM

☐ Pending
☒ Active
☒ L1: (102) "5614"
☐ Failed

DB: USPAT; US-PGPUB; EPO; JPO
 Default criteria: N/A
☒ BKR form ☒ ISR form ☒ Image ☒ Text ☒ HTML

☒ Plurals
☒ Highlight all hit terms initially

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
79	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6023074 A	20000208		Active matrix display having storage capacitor associated with each pixel t	257/59	257/350; 257/72;
80	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5994172 A	19991130		Method for producing semiconductor device	438/151	257/E21.133; 257/E21.134;
81	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5986286 A	19991116		Semiconductor device and a method of manufacturing the same	257/65	257/347; 257/350;
82	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5985769 A	19991116		Method of forming an interlayer insulating film	438/787	257/E21.243; 257/E21.278;
83	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5985740 A	19991116		Method of manufacturing a semiconductor device including redu	438/486	257/E21.133; 257/E21.413;
84	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5972105 A	19991026		Method of fabricating semiconductor device	117/8	117/933; 257/E21.133;
85	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5966594 A	19991012		Semiconductor device and method for manufacturing the same	438/151	257/E21.192; 257/E21.413;
86	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5962871 A	19991005		Method for producing semiconductor device	257/66	257/255; 257/57;
87	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5956579 A	19990921		Semiconductor, semiconductor device, and method for fabricating th	438/151	257/E21.134; 257/E21.413;
88	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5946560 A	19990831		Transistor and method of forming the same	438/162	257/57; 257/64;
89	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5929464 A	19990727		Active matrix electro-optical device	257/72	257/67; 257/E21.703
90	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5922125 A	19990713		Semiconductor device and method of manufacturing the same	117/9	117/10; 257/E21.133;
91	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5915174 A	19990622		Semiconductor device and method	438/166	257/E21.133;

EAST - [7527.wsp:1]

File View Edit Tools Window Help

Pending
Active
L1: (102) "5614"
Failed

DB: USPAT, US-PGPUB, EPO, JPO
Default operator: n/a
BRS form ISAR form Image Text HTML

Plurals
Highlight all hit terms initially

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
91	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5915174 A	19990622		Semiconductor device and method for producing the same	438/166	257/E21.133;
92	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5897347 A	19990427		Semiconductor, semiconductor device, and method for fabricating th	438/166	257/E21.318; 257/E21.134;
93	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5888858 A	19990330		Semiconductor device and fabrication method thereof	438/162	257/E21.413; 257/E21.133;
94	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5888857 A	19990330		Semiconductor device and method for manufacturing the same	438/162	257/E21.318; 257/E21.133;
95	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5886366 A	19990323		Thin film type monolithic semiconductor device	257/59	257/66; 257/70;
96	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5879977 A	19990309		Process for fabricating a thin film transistor semiconductor device	438/166	117/8; 257/66;
97	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5879974 A	19990309		Method of manufacturing a semiconductor device	438/162	148/DIG.16; 257/E21.133;
98	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5869363 A	19990209		Method of manufacturing semiconductor device	438/166	257/E21.133; 257/E21.318;
99	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5869362 A	19990209		Method of manufacturing semiconductor device	438/166	148/DIG.16; 257/E21.134;
100	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5858823 A	19990112		Semiconductor circuit for electro-optical device and method of	438/166	117/8; 257/E21.133;
101	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5818068 A	19981006		Thin film transistor circuit and an active matrix type display device	257/59	257/67; 257/72;
102	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5614733 A	19970325		Semiconductor device having crystalline thin film transistors	257/66	257/607; 257/72;

Start Inbox - Mic USPTO Intr. My Yahoo! eDAN Vers. EAST - [7527.wsp:1] 8:13 AM

EAST - [Untitled:1]

File View Edit Tools Window Help

Active

- L5: (17365) crystalli\$6 with catalyst
- L7: (2090) (crystalli\$6 with catalyst) with amorphous
- L8: (374) 7 and (crystalli\$6 with catalyst) with (heat\$3 anneal\$3)
- L9: (374) 8 and (crystalli\$6 catalyst heat\$3 anneal\$3 cryatal)
- L10: (124) 9 and ((hydrogen 'H2') with amorphous)
- L11: (380) 7 and (crystalli\$6 with catalyst) with (heat\$3 anneal\$3 irradiat\$4)
- L12: (128) 11 and ((hydrogen 'H2') with amorphous)
- L13: (83) 12 and ((substrate wafer) with (insulat\$ dielectric))
- L14: (83) 13 and silicon

Failed

Browse Queue Clear

DB: USPAT:1 ☒ Plurals

Default operator: ☒ Highlight all hit terms initially

13 and silicon

B... L... 23m 531 88H

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	<input type="checkbox"/>	<input type="checkbox"/>	US 20030134459 A1	20030717	15	Semiconductor device and manufacturing method thereof	438/151	
2	<input type="checkbox"/>	<input type="checkbox"/>	US 20030109085 A1	20030612	30	Semiconductor device, and method of forming the same	438/148	
3	<input type="checkbox"/>	<input type="checkbox"/>	US 20030102480 A1	20030605	36	Semiconductor thin film and semiconductor device	257/72	257/59; 257/E21.133;
4	<input type="checkbox"/>	<input type="checkbox"/>	US 20030067004 A1	20030410	32	Crystalline semiconductor film, method of manufacturing the same, a	257/66	438/151; 438/166;
5	<input type="checkbox"/>	<input type="checkbox"/>	US 20030032267 A1	20030213	32	Method for forming crystalline semiconductor film and apparatus for	438/486	
6	<input type="checkbox"/>	<input type="checkbox"/>	US 20030030052 A1	20030213	12	Crystalline silicon thin film semiconductor device, crystalline silic	257/65	257/E29.336
7	<input type="checkbox"/>	<input type="checkbox"/>	US 20030013280 A1	20030116	115	Semiconductor thin film forming method, production methods for sem	438/487	117/84; 117/88;
8	<input type="checkbox"/>	<input type="checkbox"/>	US 20030010980 A1	20030116	72	Semiconductor device and method for manufacturing same	257/65	
9	<input type="checkbox"/>	<input type="checkbox"/>	US 20020151154	20021017	32	Heat treatment apparatus and heat	438/502	

Start Inbox - Microsoft My Yahoo! Net EAST - [Un... 9 (07) 00:00 CD 2:43 PM

EAST - [Untitled1:1]

File View Edit Tools Window Help

Active

- L5: (17365) crystalli\$6 with catalyst
- L7: (2090) (crystalli\$6 with catalyst) with amorphous
- L8: (374) 7 and (crystalli\$6 with catalyst) with (heat\$3 anneal\$3)
- L9: (374) 8 and (crystalli\$6 catalyst heat\$3 anneal\$3 cryatal)
- L10: (124) 9 and ((hydrogen 'H2') with amorphous)
- L11: (380) 7 and (crystalli\$6 with catalyst) with (heat\$3 anneal\$3 irradiat\$4)
- L12: (128) 11 and ((hydrogen 'H2') with amorphous)
- L13: (83) 12 and ((substrate wafer) with (insulat\$ dielectric))
- L14: (83) 13 and silicon

BROWSE

Queue

Clear

DBs:

USPAT:1

Plurals

Default operator:

Highlight all hit terms initially

13 and silicon

B...

I...

Im

T...

H...

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRel
10	<input type="checkbox"/>	<input type="checkbox"/>	US 20020146874 A1	20021010	48	Method for manufacturing a semiconductor device	438/166	
11	<input type="checkbox"/>	<input type="checkbox"/>	US 20020134981 A1	20020926	43	Semiconductor device and manufacturing method of the same	257/62	257/56; 257/58;
12	<input type="checkbox"/>	<input type="checkbox"/>	US 20020132455 A1	20020919	14	Method for forming crystalline silicon layer and crystalline silicon semicond	438/486	257/E21.133; 438/482
13	<input type="checkbox"/>	<input type="checkbox"/>	US 20020132383 A1	20020919	46	Method of manufacturing a semiconductor device	438/17	257/E21.703; 257/E27.111;
14	<input type="checkbox"/>	<input type="checkbox"/>	US 20020119606 A1	20020829	49	Method of manufacturing a semiconductor device	438/149	257/E21.703; 257/E27.111;
15	<input type="checkbox"/>	<input type="checkbox"/>	US 20020113248 A1	20020822	44	Light emitting device and method of manufacturing the same	257/187	257/184; 257/290;
16	<input type="checkbox"/>	<input type="checkbox"/>	US 20020102776 A1	20020801	43	Semiconductor device and method of manufacturing the same	438/149	438/29
17	<input type="checkbox"/>	<input type="checkbox"/>	US 20020094612 A1	20020718	60	Method of manufacturing semiconductor device	438/149	438/143; 438/471
18	<input type="checkbox"/>	<input type="checkbox"/>	US 20020071072 A1	20020613	21	Display device	349/110	

Start

Inbox - Microsoft Outlook

My Yahoo! - Netscape

EAST - [Untitled1:1]

01:00:00 - CD Player

2:43 PM

EAST - [Untitled1:1]

File View Edit Tools Window Help

Active

L5: (17365) crystalli\$6 with catalyst

L7: (2090) (crystalli\$6 with catalyst) with amorphous

L8: (374) 7 and (crystalli\$6 with catalyst) with (heat\$3 anneal\$3)

L9: (374) 8 and (crystalli\$6 catalyst heat\$3 anneal\$3 cryatal)

L10: (124) 9 and ((hydrogen 'H2') with amorphous)

L11: (380) 7 and (crystalli\$6 with catalyst) with (heat\$3 anneal\$3 irradiat\$4)

L12: (128) 11 and ((hydrogen 'H2') with amorphous)

L13: (83) 12 and ((substrate wafer) with (insulat\$ dielectric))

L14: (83) 13 and silicon

Browse Queue Clear

DBs: USPAT:1 Plurals

Default operator: Highlight all hit terms exactly

13 and silicon

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
19	<input type="checkbox"/>	<input type="checkbox"/>	US 20020055208 A1	20020509	27	Process for fabricating semiconductor device	438/151	257/E21.134; 257/E21.413
20	<input type="checkbox"/>	<input type="checkbox"/>	US 20020047118 A1	20020425	18	Method for producing semiconductor device	257/57	257/E21.133; 257/E21.134;
21	<input type="checkbox"/>	<input type="checkbox"/>	US 20020030189 A1	20020314	48	Semiconductor device and manufacturing method thereof	257/59	257/72; 349/43;
22	<input type="checkbox"/>	<input type="checkbox"/>	US 20020005519 A1	20020117	16	Crystalline silicon semiconductor device and method for fabricating sa	257/70	257/E21.133; 257/E31.044
23	<input type="checkbox"/>	<input type="checkbox"/>	US 20010033985 A1	20011025	10	Electrostatic printing of a metallic toner applied to solid phase crystalliz	430/119	430/114; 430/126;
24	<input type="checkbox"/>	<input type="checkbox"/>	US 20010025992 A1	20011004	17	Liquid crystal display device and manufacturing method thereof	257/347	257/E21.703; 438/166
25	<input type="checkbox"/>	<input type="checkbox"/>	US 20010005606 A1	20010628	51	Laser irradiation apparatus and method of fabricating a semiconduct	438/151	257/E21.347; 372/23;
26	<input type="checkbox"/>	<input type="checkbox"/>	US 20010000011 A1	20010315	15	Method for producing semiconductor device	257/59	257/347; 257/E21.133
27	<input type="checkbox"/>	<input type="checkbox"/>	US 6599785 B2	20030729	47	Method of manufacturing a semiconductor device	438/151	438/154; 438/163

Start

Inbox - Microsoft Out

My Yahoo! - Netscape

EAST - [Untitled1:1]

[01]00:00 CD Player

2:43 PM

EAST - [Untitled1:1]

File View Edit Tools Window Help

Active

- L5: (17365) crystalli\$6 with catalyst
- L7: (2090) (crystalli\$6 with catalyst) with amorphous
- L8: (374) 7 and (crystalli\$6 with catalyst) with (heat\$3 anneal\$3)
- L9: (374) 8 and (crystalli\$6 catalyst heat\$3 anneal\$3 cryatal)
- L10: (124) 9 and ((hydrogen 'H2') with amorphous)
- L11: (380) 7 and (crystalli\$6 with catalyst) with (heat\$3 anneal\$3 irradiat\$4)
- L12: (128) 11 and ((hydrogen 'H2') with amorphous)
- L13: (83) 12 and ((substrate wafer) with (insulat\$ dielectric))
- L14: (83) 13 and silicon

USPAT.1 Plural: Highlight all hit terms initially

13 and silicon

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
37	✓	✓	US 6361912 B1	20020326	10	Electrostatic printing of a metallic toner applied to solid phase crystalliz	430/52	430/126; 438/486
38	✓	✓	US 6348367 B1	20020219	13	Method for manufacturing a semiconductor device	438/151	257/E21.133; 257/E21.413;
39	✓	✓	US 6337235 B1	20020108	24	Semiconductor device and manufacturing method thereof	438/166	134/1.2; 134/1.3;
40	✓	✓	US 6337231 B1	20020108	18	Method for producing semiconductor device	438/150	257/E21.133; 257/E21.134;
41	✓	✓	US 6326248 B1	20011204	26	Process for fabricating semiconductor device	438/151	257/E21.134; 257/E21.413;
42	✓	✓	US 6319761 B1	20011120	23	Method of fabricating a thin film transistor	438/166	257/E21.133; 257/E21.413;
43	✓	✓	US 6307214 B1	20011023	36	Semiconductor thin film and semiconductor device	257/59	257/627; 257/64;
44	✓	✓	US 6285042 B1	20010904	28	Active Matry Display	257/66	257/291; 257/350;
45	✓	✓	US 6251712 B1	20010626	14	Method of using phosphorous to better crystallization catalyst in a n-tv	438/143	438/154

Start Inbox - Microsoft Out My Yahoo! Netscape EAST - [Untitled1:1] [01:00:00] CD Player 2:44 PM